

DescriptionBackground of the InventionField of the invention

The present invention relates to an improvement in a process for producing superconducting films. More particularly, it relates to an improved process for producing thallium type superconducting thin films of thallium containing-compound oxides such as Tl-Ba-Ca-Cu type oxide having higher critical current density (J_c) as well as a high critical temperature (T_c).

Description of the related art

The superconductivity is a phenomenon which is explained to be a kind of phase change of electrons under which the electric resistance become zero and the perfect diamagnetism is observed. Under the superconducting condition, electric current of high density flow continuously without any loss of power, so that the power loss of about 7 % which is lost in the electric power transmission today can be saved greatly when the technology of superconductivity can be applied to the electric power transmission. Development of superconductor is also demanded in the field of measurement in order to detect very weak magnetism by SQUID, in the field of medical treatment by π -neutrons and in the field of high-energy physical experiments. Superconductor is also requested in the field of electromagnets for generating a strong magnetic field in order to develop the technologies of fusion power generation, MHD power generation, magnetic levitation trains and magnetically propelling ships. The critical temperature " T_c " of superconductors, however, could not exceed 23.2 K of Nb_3Ge which was the highest T_c for the past ten years.

The possibility of an existence of new types of superconducting materials having much higher T_c was revealed by Bednorz and Müller, who discovered a new oxide type superconductor in 1986 (Z. Phys. B64, 1986 p 189).

The new type compound oxide superconductor discovered by Bednorz and Müller is represented by $[La,Sr]_2CuO_4$ which is called the K_2NiF_4 -type oxide having a crystal structure which is similar to known perovskite type oxides. The K_2NiF_4 -type compound oxides show such higher T_c as 30 K which are extremely higher than known superconducting materials. After then, a variety of compound oxides which show much higher critical temperatures were reported and hence the possibility of an actual utilization of the high T_c superconductors have burst onto the scene.

C. W. Chu et al. reported another superconducting material of so-called YBCO type represented by $YBa_2Cu_3O_{7-x}$ having the critical temperature of about 90 K (Physical Review letters, Vol. 58, No. 9, p 908). Maeda et al reported the other type new superconducting compound oxide of Bi-Sr-Ca-Cu-O system (Japanese Journal of Applied Physics. Vol. 27, No. 2, p 1209 to 1210).

Thallium type compound oxides are also high T_c superconductors of more than 100 K. The present inventors disclosed several kinds of thallium type compound oxides superconductors in a US patent application No. 223,634 filed on July 25, 1988 and Hermann et al. reported Tl-Ba-Ca-Cu-O system in Appl. Phys. Lett. 52 (20) p 1738). Thallium type compound oxides are chemically much stable than the abovementioned YBCO type compound oxide and have such a very important merit that high T_c superconductors of higher than 100 K can be realized without using rare earth elements as a material so that the production cost can be reduced.

The above-mentioned new types oxide superconducting materials can be prepared in a form of a thin film on a substrate by physical vapour deposition (PVD) technique or chemical vapor deposition (CVD) technique.

In the case of production of thallium type oxide superconductors, however, there is a special problem, because thallium (Tl) is a very volatile element and toxic for human. In fact, thallium type superconducting thin films prepared by the conventional physical vapour technique show relatively lower T_c (critical temperature) and J_c (critical current density) than a bulk or a block of this compound oxide which is prepared by sintering technique. It is thought that this deference may be caused by shortage of oxygen in the crystal of which the superconducting thin film is made.

Heretofore, it is a usual practice to anneal a deposited thin film at 600 to 900 °C in the presence of oxygen gas in order to improve the superconducting properties of oxide type superconducting thin films deposited. This technique, however, is not effective in the case of thallium type superconducting thin films because thallium has a high vapour pressure and hence a majority of thallium atoms in the thin film escape from the thin film, so that the resulting thin film doesn't show desired high T_c and J_c .

A heat treatment in which a piece of elemental thallium (Tl) is placed together with the thin film inside the furnace is presented by Shih and Qiv in Applied Physics Letters, Vol. 53, No. 6, pages 523-525.

Therefore, an object of the present invention is to overcome the problem of the prior arts and to provide an improved process for producing superconducting thin films of thallium (Tl) type compound oxides.

Summary of the Invention

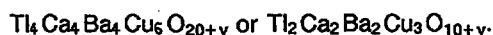
The present invention provides a process for producing a superconducting thin film of thallium type compound oxide, comprising depositing a thin film of thallium-containing compound oxide on a substrate by physical vapour deposition method or chemical vapour deposition method and then subjecting the resulting thin film to heat-treatment, characterized in that the heat-treatment is effected at a temperature between 880 °C and 920 °C for a predetermined time under a partial pressure of thallium oxide higher than the saturated vapour pressure of thallium oxide at the temperature.

Preferably, the resulting heat-treated thin film is further subjected to secondary heat-treatment which is effected at a temperature between 600 °C and 900 °C for a predetermined time under a partial pressure of thallium oxide lower than the saturated vapour pressure of thallium oxide at said temperature.

The present invention is applicable for any superconducting thin film of compound oxide containing thallium (Tl). One of the typical thallium type compound oxide is represented by the general formula:



in which m, n, x and y are numbers each satisfying ranges of $6 \leq m \leq 16$, $4 \leq n \leq 12$, $0.2 < x < 0.8$ and $-2 \leq y \leq +2$, respectively and $p = (6 + m + n)$. For example, this type can have following compositions:



As the other type thallium-containing compound oxides to which the present invention is applicable, it can be mentioned the following systems:

- Tl-Sr-Ca-Cu-O system (75 to 100 K),
- Tl-Pb-Sr-Ca-Cu-O system (80 to 122 K),
- Tl-Pb-Ba-Ca-Cu-O system (90 to 122 K),
- (Tl, La, Pb)-Sr-Ca-Cu-O system (100 K),
- Tl-Ba-(Y, Ca)-Cu-O system (92 K),
- Tl-Pb-Ca-Ce-Sr-Cu-O system (95 K),
- Tl-Ba-Ce-Cu-O system (90 K),
- (Tl, Ln)-Sr-Ca-Cu-O system (80 to 90 K),
- (Bi, Tl)-Sr-Cu-O system (90 K),
- Pb-Tl-Sr-Cu-O system (42 K),
- La-Tl-Sr-Cu-O system (37 K) and
- Nd-Tl-Sr-Cu-O system (44 K),
- Tl-Bi-Sr-Ca-Cu-O system (25 K).

(note) Ln : lanthanoid

The superconducting thin film according to the present invention can be deposited on a substrate by physical vapour deposition (PVD) technique such as RF sputtering, vacuum deposition, ion-plating, MBE or by chemical vapor deposition (CVD) technique such as thermal CVD, plasma CVD, photo CVD, MOCVD or the like.

When RF magnetron sputtering, vacuum deposition or ion-plating method is used as the physical vapour deposition technique, the atomic ratios of metal elements contained in a vapour source or a target is adjusted according to difference in the evaporation rate as well as difference in adsorption rate of metal elements to the substrate. The vapour source is preferably a sintered mass which is prepared by powder-sintering technique of a material power mixture comprising metal elements and/or their oxides or carbonates or a sintered powder which is obtained by pulverizing the sintered mass. The vapour source can be also divided into a plurality of segments.

In the case of the molecular beam epitaxy (MBE), elemental metals of Tl, Ba, Ca and Cu or their compounds such as their oxides, carbonates, fluorides or the like are evaporated by means of a K-cell or an ion beam gun. In this case, oxygen is supplied, if necessary, separately or additionally into an evaporation atmosphere.

For example, a vapour source or a target for preparing a thin film of Tl-Ba-Ca-Cu-O type compound oxide is prepared as following:

At first, a powder mixture is prepared by mixing powders of compounds of Ba, Ca and Cu such as their oxides, carbonates, fluorides or the like. The powder mixture is then subjected to preliminary sintering operation and pulverization. The resulting preliminary sintered powder is mixed with a powder of thallium compound such as thallium oxide, thallium carbonate or thallium fluoride and is sintered finally. The resulting sintered mass thus obtained can be used directly or after pulverization as a vapour source, particularly, as a target for sputtering. This preparation method is very effective to adjust the atomic ratios of the vapour source or target because thallium is a very volatile and toxic element.

In either case, the composition of the thin film deposited can be varied in a wide range by adjusting the composition in the vapour source and/or by selecting a suitable combination of vapour sources. Generally speaking, supplement of oxygen into the evaporation atmosphere is ensured either by evaporating oxygen-containing compounds such as oxides or carbonates of Tl, Ba, Ca and Cu or by supplying oxygen gas separately into a vacuum chamber. In any case, the oxygen contents in the atmosphere during deposition of the superconducting thin film must be controlled precisely in order to adjust the oxygen deficiency which is a critical factor to realize a superconducting thin film of high T_c on the substrate to a predetermined value.

The substrate on which the thin film is deposited can be a single crystal of MgO, SrTiO₃, LaAlO₃, LaGaO₃ or the like. When a single crystal of silicon is used as a substrate, it is preferable to cover a surface of the silicon substrate with a buffer layer such as MgO or ZrO₂. The superconducting thin film according to the present invention is preferably deposited on a {001} plane or {110} plane of these single crystals. In the course of the vapour deposition, the substrate is heated at a temperature between a room temperature and 500 °C.

Essence of the present invention reside in that a thin film of thallium type compound oxide deposited on a substrate by physical vapour deposition method or chemical vapour deposition method is heat-treated at a temperature between 880 °C and 920 °C for a predetermined time under a partial pressure of thallium oxide vapour higher than the saturated vapour pressure of thallium oxide at said temperature.

The present inventors confirmed such a fact that the thin film prepared according to the present invention shows a very smooth surface and is very homogeneous in composition which is thought to be one reason why the thin film according to the present invention show very high T_c and J_c . In other words, the heat-treatment according to the present invention is effective to suppress escape of thallium vapour out of the thin film and to promote proper crystallization of the thin film.

When the temperature of heat-treatment is not higher than 880 °C, a uniform smooth thin film can not be obtained because a mixture of different phases each having a different critical temperature is produced so that the total T_c of the thin film become lower. To the contrary, if the temperature of heat-treatment is not lower than 920 °C, the evaporation of thallium (Tl) increase excessively so that it is difficult to adjust the composition of the thin film to desired atomic ratios and also it increases precipitates which doesn't contribute the superconductivity.

This first heat-treatment is effected preferably for a time duration between 1 minute and 10 hours. Advantage of the heat-treatment according to the present invention can't be expected if the heating time is not longer than 1 minute, while longer heat-treatment than 10 hours may not effective to improve the superconducting property.

In a preferred embodiment, the resulting heat-treated thin film is further subjected to secondary heat-treatment which is effected at a temperature between 600 °C and 900 °C for a predetermined time under a partial pressure of thallium oxide vapour lower than the saturated vapour pressure of thallium oxide at the temperature. This secondary heat-treatment is effective to remove or drive off excess thallium atom trapped in the thin film during the first heat-treatment so that the atomic ratio of thallium atom in the final product is adjusted to a desired stoichiometric proportion. This secondary heat-treatment is preferably continued for a time duration between 5 minutes and 50 hours.

The above-mentioned heat-treatment condition that the partial pressure of thallium oxide become higher or lower than the saturated vapour pressure of thallium oxide at the temperature can be realized easily by carrying out the heat-treatment in the presence of thallium vapor and oxygen gas. In a simplest case, thallium oxide is used as a vapour source for realizing the condition. Another preferable vapour source is a thallium-containing compound such as Tl-Ba-Ca-Cu-O type compound oxide. In a variation, thallium gas and oxygen gas are supplied under control into a chamber in which the heat-treatment is effected.

In a preferred embodiment of the present invention, the condition is realized by creating a temperature gradient in a closed space in which the substrate having the thin film and a thallium oxide vapour source are placed in such a manner that the thallium oxide vapour source is heated at a higher temperature than

the substrate. In this case the closed spaced is preferably delimited by a pipe made of precious metal such as silver (Ag) and having an opening communicating with an interior of the chamber.

In the heat-treatments, oxygen gas is always supplied into the atmosphere in addition to thallium oxide gas so that the oxygen contents in the thin film is also adjusted to the desired stoichiometric proportion.

Now, the process according to the present invention is described with reference to Fig. 1 which illustrate one embodiment of how to carry out the present process.

Brief Description of the Drawing

Fig. 1 is a drawing illustrating how to carry out the process according to the present invention.

A substrate (1) on which a thin film of thallium type compound oxide is deposited is placed in a pipe (4) made of silver (Ag) having an opening at an extreme end. In the silver pipe (4), a vapour source of thallium oxide (2) such as powder of thallium oxide is also placed. The vapour source of thallium oxide (2) can be a sintered mass or powder which is used for preparing the thin film deposited on the substrate in the physical vapour deposition stage.

The silver pipe (4) is set in a sintering furnace (5) into which oxygen gas (O_2) is supplied so that oxygen gas can penetrate into the silver pipe through its open end. Usually, the oxygen gas pressure can be about at ambient pressure (1 atm) but the heat-treatment can be effected also at a higher oxygen pressure than 1 atm.

In operation, a temperature gradient is created in the sintering furnace (5) in such a manner that substrate (1) on which a thin film of thallium type compound oxide is deposited is heated at a temperature T_2 , while the vapour source of thallium oxide (2) is heated at a temperature T_1 respectively. The temperature T_1 is higher than the temperature T_2 , for example, $T_1 = 930^\circ C$ and $T_2 = 900^\circ C$, so that the heat-treatment of the thin film deposited on the substrate (1) is effected at $T_2 = 900^\circ C$ in thallium oxide vapour produced from the vapour source (2) which is heated at a relatively higher temperature than the substrate (1). Under the above-mentioned temperature gradient, the vapour pressure of thallium oxide gas in the neighborhood of the thin film become higher than the saturated vapour pressure of thallium oxide (over-saturated vapour pressure). This first heat-treatment is continued for a desired time duration, usually more than one hour.

After this first heat-treatment complete, a second heat-treatment is effected in the same apparatus except that the temperatures of T_1 and T_2 are lowered to an equal temperature such as $T_1 = T_2 = 850^\circ C$ for a desired time duration, usually more than one hour.

The process according to the present invention has the following merits:

(1) It is possible to adjust the atomic ratio of thallium in the thin film of compound oxide to a desired value, because the heat-treatment is effected in the saturated vapour pressure of volatile thallium so that escape of thallium atom out of the thin film is suppressed.

(2) It is also possible to adjust the oxygen contents in the thin film to a desired value because the heat-treatment is carried out in oxygen-rich condition.

(3) The thin film is not contaminated because the heat-treatment is effected in a pipe made of precious metal which is inactive to the thin film.

In a conclusion, according to the process of the present invention, it becomes possible to producing high-quality superconducting thin film of thallium-containing compound oxides such as Tl-Ba-Ca-Cu type oxide superconductor improved in superconducting property, particularly in the critical current density J_c in a stable condition.

Now, the method according to the present invention is described with reference to Examples but the scope of the present invention should not limited to the following Examples.

Example 1

Preparation of thin film of thallium type compound oxide

A thin film of thallium type compound oxide is deposited on a substrate of MgO single crystal by RF magnetron sputtering.

(1) Preparation of a target

Powders of $BaCO_3$ and CuO are kneaded in a mortar. The resulting powder mixture is sintered preliminarily at $900^\circ C$ for 8 hours. The resulting sintered mass is pulverized to a powder to which powders

of Tl_2O_3 and CaO are admixed uniformly to prepare a material powder mixture. The atomic ratios of Tl : Ca : Ba : Cu in the material powder mixture are adjusted to 2.4 : 2.3 : 2.0 : 3.0.

The material powder mixture is pressed to a compact which is then wrapped by a foil made of gold (Au). The compact wrapped by the gold foil is then sintered is 905 °C for 3 hours in oxygen gas atmosphere in a sintering furnace.

(2) Deposition of a thin film

The resulting sintered mass is pulverized to obtain a sintered powder which is used as a powder target for RF magnetron sputtering which is carried out under the following conditions:

Substrate : {100} plane of a single crystal of MgO

Substrate temperature : 350 °C

High-frequency power : 0.64 W/cm²

Sputtering gas : a mixed gas of Ar and O₂

O₂/(Ar+O₂) = 0.2 (vol)

Sputtering pressure : 5×10^{-2} Torr

The resulting thin film is an amorphous film having a composition of Tl:Ba:Ca:Cu = 2:2:2:3 and doesn't show superconducting property.

Heat-treatment according to the invention

The resulting substrate on which the thin film of thallium-containing compound oxide is deposited is heat-treated in a furnace illustrated in Fig. 1.

Namely, the substrate (1) is placed in a pipe made of silver (Ag) having an open end. In the silver pipe (4), a compound of Tl-Ba-Ca-Cu-O (2) which was prepared by the same method as is described in the "(1) preparation of a target" is also placed. This sintered mass (2) is prepared by the same process described in the preparation of the target.

Then, the silver pipe (4) is set in a sintering furnace (5) into which oxygen gas (O₂) of one atm is supplied.

A temperature gradient is created in the sintering furnace (5) in such a manner that substrate (1) is heated at 900 °C (T₂), while the Tl-Ba-Ca-Cu-O compound (2) is heated at 930 °C (T₁) respectively.

Under this temperature gradient, the vapour pressure of thallium oxide gas in the neighborhood of the substrate (1) become higher than the saturated vapour pressure of thallium oxide at 900 °C (over-saturated vapour pressure). This first heat-treatment is continued for one hour.

After this first heat-treatment complete, second heat-treatment is effected in the same apparatus except that the temperatures of T₁ and T₂ are lowered to an equal temperature of T₁ = T₂ = 850 °C. Under this temperature gradient, the vapour pressure of thallium oxide gas in the neighborhood of the substrate (1) become lower than the saturated vapour pressure of thallium oxide at 850 °C. This secondary heat-treatment is continued for three hours.

The resulting superconducting thin film is evaluated by measuring the critical temperature T_c, the critical current density J_c and by observing their surfaces by a scanning electron microscope (SEM).

The critical temperatures T_c is determined by usual four probe method. Temperature is measured by a calibrated Au(Fe)-Ag thermocouple. The critical current density (J_c) of the thin film obtained is determined at 77.0 K and is expressed by A/cm².

The results is shown in Table 1.

Table 1

T _c (K)	125 K
J _c (77K)	3.2 x 10 ⁶ A/cm ² .
Surface condition	smooth and uniform

10 Comparative example 1

The Example 1 is repeated except that the first heat-treatment is omitted. Namely, the heat-treatment is effected in the same condition as the secondary condition which corresponds to the prior art.

The result on this case is shown in Table 2.

Table 2

T _c (K)	103 K
J _c (77K)	1.2 x 10 ⁴ A/cm ²
Surface condition	rough and not uniform

Comparing Example 1 with Comparative Example 1, it is apparent that the superconducting property, particularly the critical current density improve remarkably.

Example 2

The Example 1 is repeated except that the target is changed to prepare a different thin film of compound oxide having the following proportion:



In this case, the target is prepared as following: at first, a powder mixture of Ba₂O₃, CaO, SrCO₃ and CuO is sintered preliminarily at 700 °C for 10 hours. The resulting sintered mass is pulverized to a powder to which powder of Ti₂O₃ is admixed uniformly to prepare a material powder mixture which is sintered finally at 910 °C for 3 hours in the same manner as Example 1. The atomic ratios of the sintered mass are Ti : Bi : Ca : Sr : Cu = 1 : 0.3 : 2.1 : 2 : 3.

A thin film is prepared and evaluated by the same method as Example 1. The result on this case is shown in Table 3.

Table 3

T _c (K)	115 K
J _c (77K)	3.1 x 10 ⁶ A/cm ²
Surface condition	smooth and uniform

Comparative example 2

The Example 2 is repeated except that the first heat-treatment is omitted. Namely, the heat-treatment is effected in the same condition as the secondary condition which corresponds to the prior art.

The result on this case is shown in Table 4.

Table 4

T _c (K)	92 K
J _c (77K)	1.2×10^4 A/cm ²
Surface condition	rough and not uniform

10 Example 3

The Example 1 is repeated except that the vapour source is changed to a powder of thallium oxide (Tl₂O₃) and that the thallium oxide powder is heated at 910 °C (T₁) and while the substrate is heated at 900 °C (T₂) in the first heat-treatment for 30 minute.

15 The resulting thin film heat-treated is evaluated by the same method as Example 1. The result on this case is shown in Table 5.

Table 5

T _c (K)	124 K
J _c (77K)	3.5×10^6 A/cm ²
Surface condition	smooth and uniform

Claims

1. A process for producing a superconducting thin film of thallium type compound oxide, comprising depositing a thin film of thallium-containing compound oxide on a substrate by physical vapour deposition method or chemical vapour deposition method and then subjecting the resulting thin film to heat-treatment, characterized in that said heat-treatment is effected at a temperature between 880 °C and 920 °C for a predetermined time under a partial pressure of thallium oxide higher than the saturated vapour pressure of thallium oxide at said temperature.
2. The process set forth in Claim 1 wherein the resulting heat-treated thin film is subjected to secondary heat-treatment which is effected at a temperature between 600 °C and 900 °C for a predetermined time under a partial pressure of thallium oxide lower than the saturated vapour pressure of thallium oxide at said temperature.
3. The process set forth in Claim 1 or 2 wherein the first and second heat-treatment is effected in oxygen-containing atmosphere.
4. The process set forth in any one of Claim 1 to 3 wherein the first and/or second heat-treatment is effected in a partially closed space delimited in a furnace.
5. The process set forth in Claim 4 wherein said partially closed space is formed by a pipe made of precious metal having an opening communicating with an interior space of the furnace.
6. The process set forth in any one of Claim 1 to 5 wherein said condition that the partial pressure of thallium oxide become higher than the saturated vapour pressure of thallium oxide at said temperature is created by heating a thallium-containing compound at a temperature which is higher than said temperature at which said thin film is heat-treated.
7. The process set forth in Claim 6 wherein said thallium-containing compound oxide is thallium oxide.
8. The process set forth in Claim 6 wherein said thallium-containing compound oxide is a compound having the same composition as said thin film to be heat-treated.

Table 4

Tc (K)	92 K
Jc (77K)	1.2×10^4 A/cm ²
Surface condition	rough and not uniform

10 Example 3

The Example 1 is repeated except that the vapour source is changed to a powder of thallium oxide (Tl₂O₃) and that the thallium oxide powder is heated at 910 °C (T₁) and while the substrate is heated at 900 °C (T₂) in the first heat-treatment for 30 minute.

15 The resulting thin film heat-treated is evaluated by the same method as Example 1. The result on this case is shown in Table 5.

Table 5

Tc (K)	124 K
Jc (77K)	3.5×10^6 A/cm ²
Surface condition	smooth and uniform

Claims

1. A process for producing a superconducting thin film of thallium type compound oxide, comprising
30 depositing a thin film of thallium-containing compound oxide on a substrate by physical vapour deposition method or chemical vapour deposition method and then subjecting the resulting thin film to heat-treatment, characterized in that said heat-treatment is effected at a temperature between 880 °C and 920 °C for a predetermined time under a partial pressure of thallium oxide higher than the saturated vapour pressure of thallium oxide at said temperature.
2. The process set forth in Claim 1 wherein the resulting heat-treated thin film is subjected to secondary
35 heat-treatment which is effected at a temperature between 600 °C and 900 °C for a predetermined time under a partial pressure of thallium oxide lower than the saturated vapour pressure of thallium oxide at said temperature.
3. The process set forth in Claim 1 or 2 wherein the first and second heat-treatment is effected in oxygen-
40 containing atmosphere.
4. The process set forth in any one of Claim 1 to 3 wherein the first and/or second heat-treatment is
45 effected in a partially closed space delimited in a furnace.
5. The process set forth in Claim 4 wherein said partially closed space is formed by a pipe made of
precious metal having an opening communicating with an interior space of the furnace.
- 50 6. The process set forth in any one of Claim 1 to 5 wherein said condition that the partial pressure of thallium oxide become higher than the saturated vapour pressure of thallium oxide at said temperature is created by heating a thallium-containing compound at a temperature which is higher than said temperature at which said thin film is heat-treated.
- 55 7. The process set forth in Claim 6 wherein said thallium-containing compound oxide is thallium oxide.
8. The process set forth in Claim 6 wherein said thallium-containing compound oxide is a compound having the same composition as said thin film to be heat-treated.



9. The process set forth in any one of Claim 1 to 8 wherein said first and secondary heat-treatment is effected for more than one minute.

10. The process set forth in any one of Claim 1 to 9 wherein said superconducting thin film of thallium type compound oxide has a composition represented by the general formula:



in which m, n, x and y are numbers each satisfying ranges of

$6 \leq m \leq 16$, $4 \leq n \leq 12$, $0.2 < x < 0.8$ and $-2 \leq y \leq +2$,

respectively and $p = (6 + m + n)$.

11. The process set forth in any one of Claim 1 to 10 wherein said substrate is a single crystal of MgO , SrTiO_3 , LaAlO_3 or LaGaO_3 .

Patentansprüche

1. Verfahren zur Herstellung eines supraleitenden Dünnsfilms aus einer thalliumartigen Oxidverbindung, wobei ein Dünnsfilm aus einer Thallium enthaltenden Oxidverbindung mittels des physikalischen Dampfabscheidungsverfahrens oder des chemischen Dampfabscheidungsverfahrens auf einem Substrat abgeschieden wird, wonach der so erhaltene Dünnsfilm einer Wärmebehandlung unterworfen wird, dadurch gekennzeichnet, daß die Wärmebehandlung bei einer Temperatur zwischen 880°C und 920°C für eine vorgegebene Zeit durchgeführt wird, wobei der Partialdruck des Thalliumoxids höher als der Sättigungsdampfdruck des Thalliumoxids bei dieser Temperatur ist.

2. Verfahren nach Anspruch 1, bei dem der erhaltene wärmebehandelte Dünnsfilm einer zweiten Wärmebehandlung unterworfen wird, die bei einer Temperatur zwischen 600°C und 900°C während einer vorgegebenen Zeit durchgeführt wird, wobei der Partialdruck des Thalliumoxids geringer ist als der Sättigungsdampfdruck des Thalliumoxids bei dieser Temperatur.

3. Verfahren nach Anspruch 1 oder 2, bei dem die erste und die zweite Wärmebehandlung in einer sauerstoffhaltigen Atmosphäre durchgeführt wird.

4. Verfahren nach einem der Ansprüche 1 bis 3, bei dem die erste und/oder die zweite Wärmebehandlung in einem teilweise geschlossenen in einem Ofen enthaltenen Raum durchgeführt wird.

5. Verfahren nach Anspruch 4, bei dem der teilweise geschlossene Raum durch ein Rohr aus Edelmetall gebildet wird, das eine Öffnung aufweist, die mit dem Innenraum des Ofens in Verbindung steht.

6. Verfahren nach einem der Ansprüche 1 bis 5, bei dem die Bedingung, daß der Partialdruck des Thalliumoxids höher ist als der Sättigungsdampfdruck des Thalliumoxids bei dieser Temperatur, bewirkt wird durch Erwärmen einer Thallium enthaltenden Verbindung auf eine Temperatur, die höher ist als die Temperatur, bei der der Dünnsfilm wärmebehandelt wird.

7. Verfahren nach Anspruch 6, bei dem die Thallium enthaltende Oxidverbindung Thalliumoxid ist.

8. Verfahren nach Anspruch 6, bei dem die Thallium enthaltende Oxidverbindung eine Verbindung ist, welche dieselbe Zusammensetzung aufweist, wie der mit Wärme zu behandelnde Dünnsfilm.

9. Verfahren nach einem der Ansprüche 1 bis 8, bei dem die erste und zweite Wärmebehandlung für mehr als eine Minute durchgeführt wird.

10. Verfahren nach einem der Ansprüche 1 bis 9, bei dem der supraleitende Dünnsfilm der thalliumartigen Oxidverbindung eine Zusammensetzung aufweist gemäß der allgemeinen Formel



wobei m, n, x und y Zahlen sind, die die folgenden Bedingungen erfüllen



$6 \leq m \leq 16$, $4 \leq n \leq 12$, $0,2 < x < 0,8$ und $-2 \leq y \leq +2$
bzw. $p = (6 + m + n)$.

11. Verfahren nach einem der Ansprüche 1 bis 10, bei dem das Substrat ein Einkristall aus MgO , $SrTiO_3$, $LaAlO_3$ oder $LaGaO_3$) ist.

Revendications

1. Procédé pour la fabrication d'une couche mince supraconductrice en oxyde composé du type au thallium, comprenant le dépôt d'une couche mince d'un oxyde composé contenant du thallium sur un substrat par un procédé de dépôt physique en phase vapeur ou par un procédé de dépôt chimique en phase vapeur, et ensuite l'exécution d'un traitement thermique sur la couche mince obtenue, caractérisé en ce que ledit traitement thermique est effectué à une température située entre $880^\circ C$ et $920^\circ C$ pendant une durée prédéterminée sous une pression partielle d'oxyde de thallium, supérieure à la pression de vapeur saturée de l'oxyde de thallium à ladite température.
2. Procédé selon la revendication 1, dans lequel la couche mince thermiquement traitée obtenue est soumise à un second traitement thermique, qui est effectué à une température située entre $600^\circ C$ et $900^\circ C$ pendant une durée prédéterminée sous une pression partielle d'oxyde de thallium, inférieure à la pression de vapeur saturée de l'oxyde de thallium à ladite température.
3. Procédé selon la revendication 1 ou 2, dans lequel les premier et second traitements thermiques sont effectués dans une atmosphère contenant de l'oxygène.
4. Procédé selon l'une quelconque des revendications 1 à 3, dans lequel le premier et/ou le second traitement thermique est effectué dans un espace partiellement clos, qui est délimité dans un four.
5. Procédé selon la revendication 4, dans lequel ledit espace partiellement clos est formé par un tube fait d'un métal précieux et ayant une ouverture communiquant avec un espace intérieur du four.
6. Procédé selon l'une quelconque des revendications 1 à 5, dans lequel ladite condition que la pression partielle de l'oxyde de thallium devienne plus élevée que la pression de vapeur saturée de l'oxyde de thallium à ladite température est obtenue par chauffage d'un composé contenant du thallium à une température qui est supérieure à ladite température à laquelle ladite couche mince est thermiquement traitée.
7. Procédé selon la revendication 6, dans lequel ledit oxyde composé contenant du thallium est de l'oxyde de thallium.
8. Procédé selon la revendication 6, dans lequel ledit oxyde composé contenant du thallium est un composé ayant la même composition que ladite couche mince à traiter thermiquement.
9. Procédé selon l'une quelconque des revendications 1 à 8, dans lequel lesdits premier et second traitements thermiques sont effectués pendant plus d'une minute.
10. Procédé selon l'une quelconque des revendications 1 à 9, dans lequel ladite couche mince supraconductrice en oxyde composé du type au thallium a une composition représentée par la formule générale :

$$Tl_x(Ca_{1-x}Ba_x)_mCu_nO_{p+y}$$

où m , n , x et y sont des nombres satisfaisant chacun, respectivement, aux fourchettes ci-après
 $6 \leq m \leq 16$, $4 \leq n \leq 12$, $0,2 < x < 0,8$ et $-2 \leq y \leq +2$,
et où $p = (6 + m + n)$.
11. Procédé selon l'une quelconque des revendications 1 à 10, dans lequel ledit substrat est un monocristal de MgO , $SrTiO_3$, $LaAlO_3$, ou $LaGaO_3$.

